

Gate resistor installed Dual N-channel MOSFET

KFC4A21300L Data Sheet

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1. GENERAL DESCRIPTION

Gate resistor installed Dual N-channel MOSFET
For lithium-ion secondary battery protection circuits

2. FEATURES

- Source-source ON resistance: $R_{SS(on)}$ typ. = 80 m Ω (V_{GS} = 3.8 V)
- CSP (Chip Size Package)
- RoHS compliant (EU RoHS / MSL: Level 1 compliant)

3. MARKING SYMBOL: 4D

4. PACKAGING

Embossed type (Thermo-compression sealing): 16,000 pcs / reel (standard)

5. ABSOLUTE MAXIMUM RATINGS $T_a = 25\text{ }^{\circ}\text{C}$

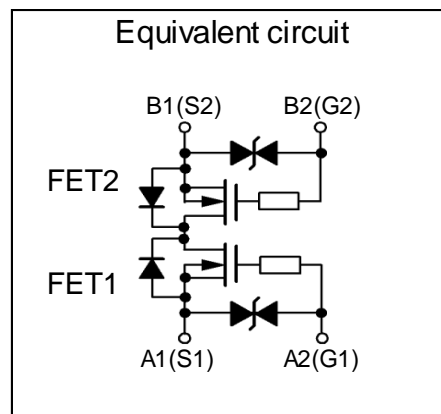
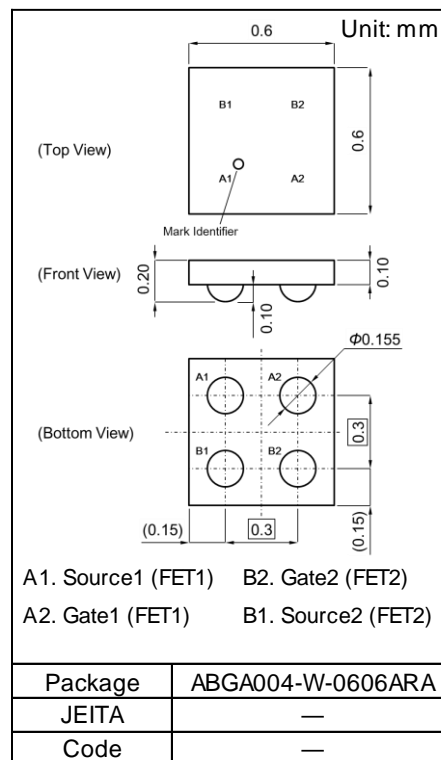
Parameter	Symbol	Rating	Unit
Source-source Voltage	VSS	12	V
Gate-source Voltage	VGS	± 8	V
Source Current (DC) ^{*1}	IS	1.5	A
Source Current (Pulsed) ^{*2}	ISp	15	A
Total Power Dissipation ^{*1}	PD	0.32	W
Channel Temperature	Tch	150	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

6. THERMAL CHARACTERISTICS $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Rating	Unit
Thermal Resistance (ch-a)	Rth ^{*1}	390	$^{\circ}\text{C} / \text{W}$

Note ^{*1} Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm),
using the recommended pad size (36 μm Copper).

^{*2} $t = 10\text{ }\mu\text{s}$, Duty Cycle $\leq 1\%$



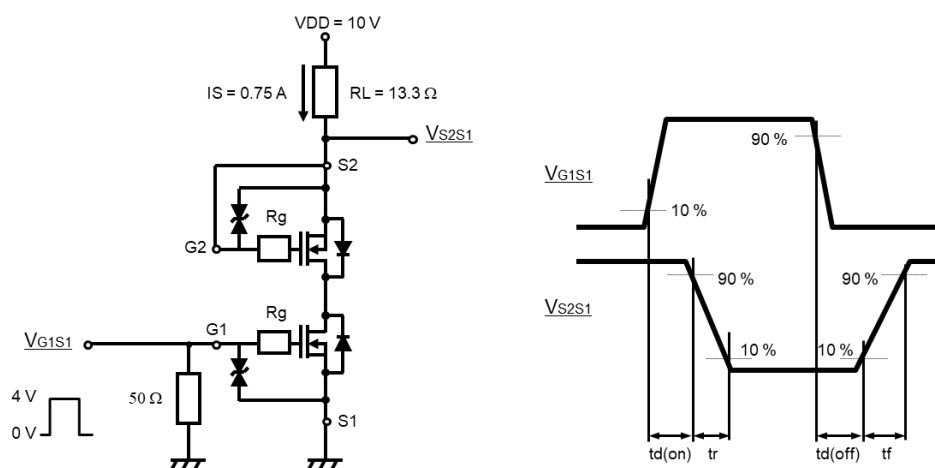
7. ELECTRICAL CHARACTERISTICS $T_a = 25\text{ }^{\circ}\text{C} \pm 3\text{ }^{\circ}\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Source-source Breakdown Voltage	VSSS	$I_S = 1\text{ mA}$, $V_{GS} = 0\text{ V}$	12			V
Zero Gate Voltage Source Current	ISSS	$V_{SS} = 12\text{ V}$, $V_{GS} = 0\text{ V}$			1.0	μA
Gate-Source Leakage Current	IGSS1	$V_{GS} = \pm 8\text{ V}$, $V_{SS} = 0\text{ V}$			± 10	μA
	IGSS2	$V_{GS} = \pm 5\text{ V}$, $V_{SS} = 0\text{ V}$			± 1.0	
Gate-source Threshold Voltage	V_{th}	$I_S = 0.03\text{ mA}$, $V_{SS} = 10\text{ V}$	0.35	0.90	1.40	V
Source-source On-state Resistance	RSS(on)1	$I_S = 0.75\text{ A}$, $V_{GS} = 4.5\text{ V}$	55	70	95	$\text{m}\Omega$
	RSS(on)2	$I_S = 0.75\text{ A}$, $V_{GS} = 3.8\text{ V}$	60	80	110	
	RSS(on)3	$I_S = 0.75\text{ A}$, $V_{GS} = 3.1\text{ V}$	65	90	150	
	RSS(on)4	$I_S = 0.75\text{ A}$, $V_{GS} = 2.5\text{ V}$	70	115	225	
Body Diode Forward Voltage	$V_{F(s-s)}$	$I_F = 0.75\text{ A}$, $V_{GS} = 0\text{ V}$		0.6	1.2	V
Input Capacitance ^{*1}	Ciss	$V_{SS} = 10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ kHz}$		115		pF
Output Capacitance ^{*1}	Coss			25		
Reverse Transfer Capacitance ^{*1}	Crss			18		
Turn-on delay Time ^{*1,*2}	$t_{d(on)}$	$V_{DD} = 10\text{ V}$, $V_{GS} = 0\text{ to }4\text{ V}$ $I_S = 0.75\text{ A}$		0.10		μs
Rise Time ^{*1,*2}	t_r			0.20		
Turn-off delay Time ^{*1,*2}	$t_{d(off)}$	$V_{DD} = 10\text{ V}$, $V_{GS} = 4\text{ to }0\text{ V}$ $I_S = 0.75\text{ A}$		0.27		μs
Fall Time ^{*1,*2}	t_f			0.22		
Total Gate Charge ^{*1}	Q_g	$V_{DD} = 10\text{ V}$ $V_{GS} = 0\text{ to }4\text{ V}$ $I_S = 0.75\text{ A}$		1.7		nC
Gate-source Charge ^{*1}	Q_{gs}			0.5		
Gate-drain Charge ^{*1}	Q_{gd}			0.45		

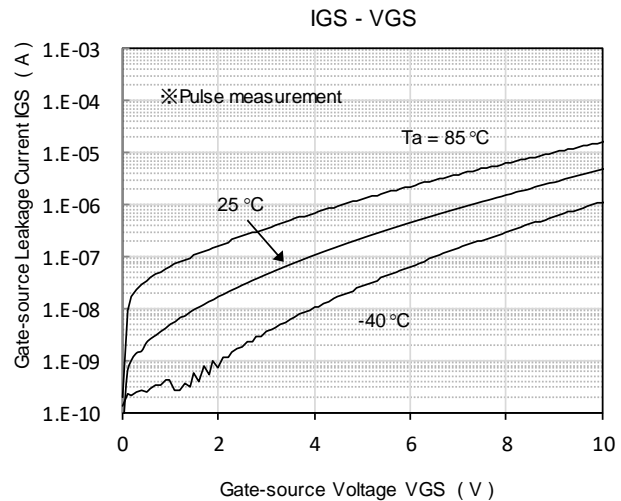
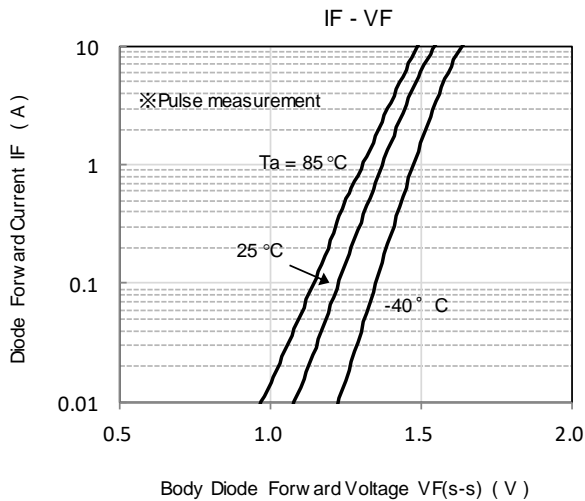
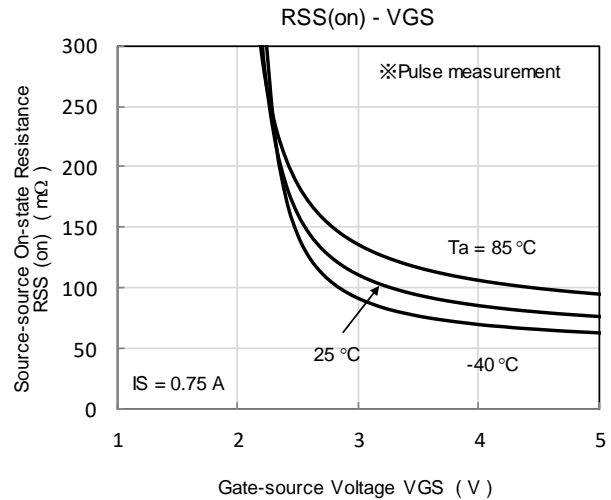
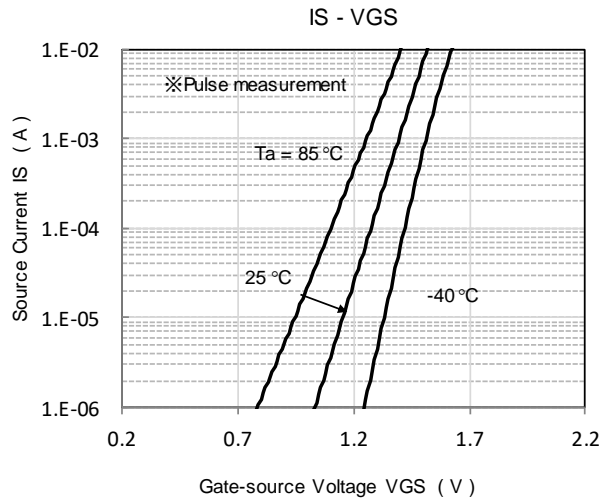
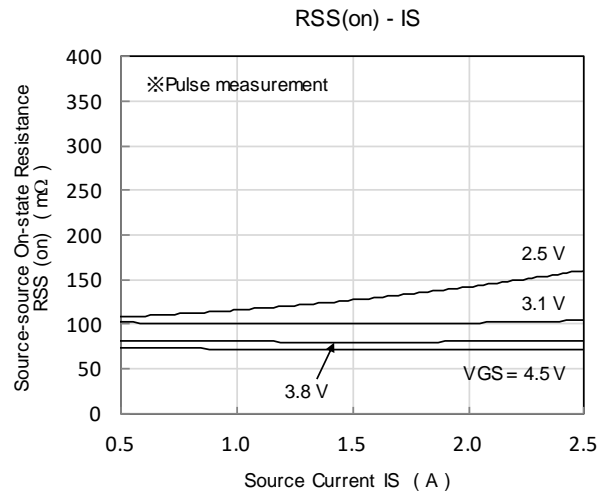
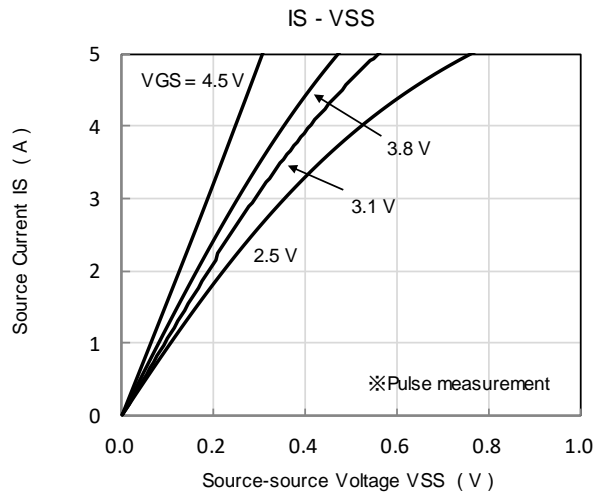
Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

*1 Guaranteed by design, not subject to production testing

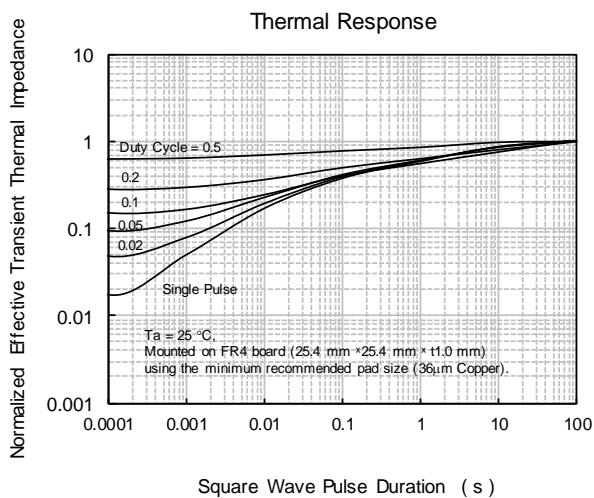
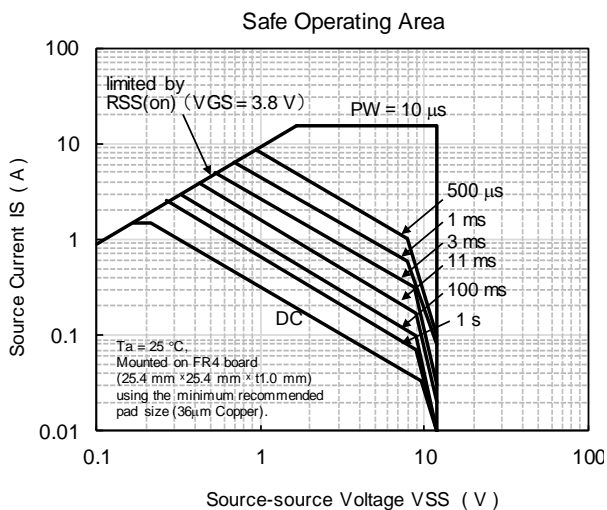
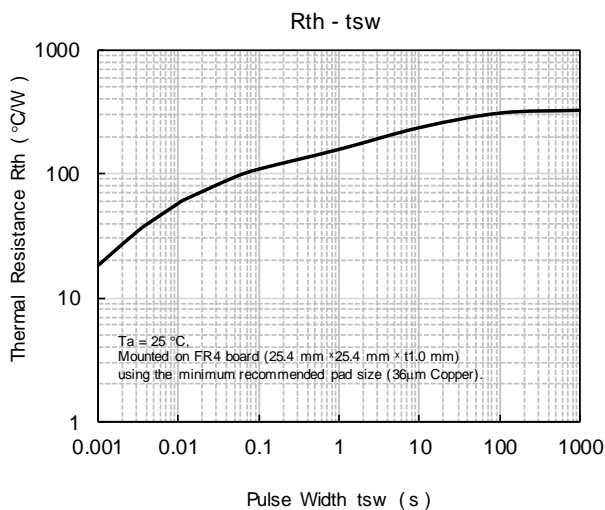
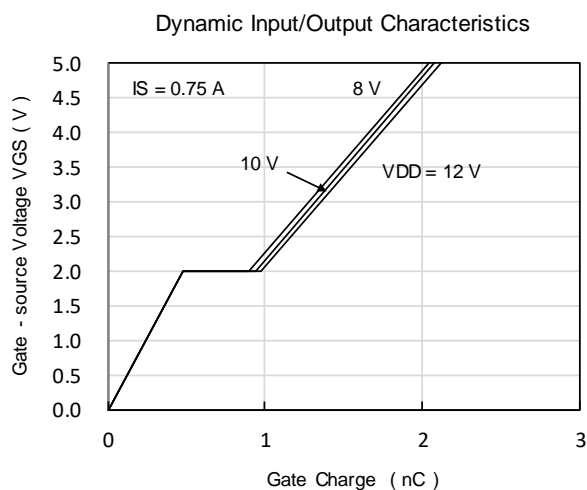
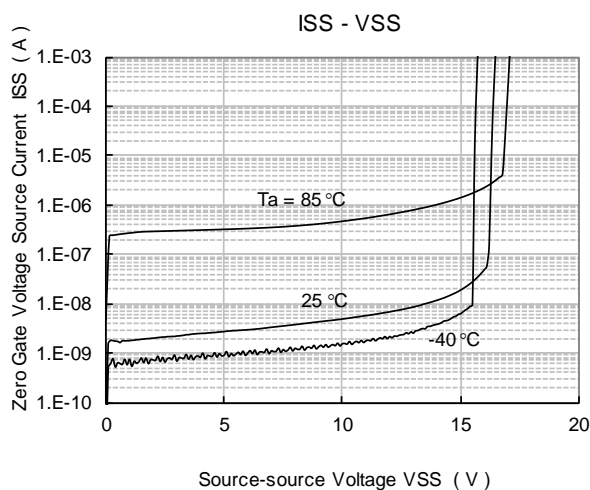
*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



8. TECHNICAL DATA (Reference)

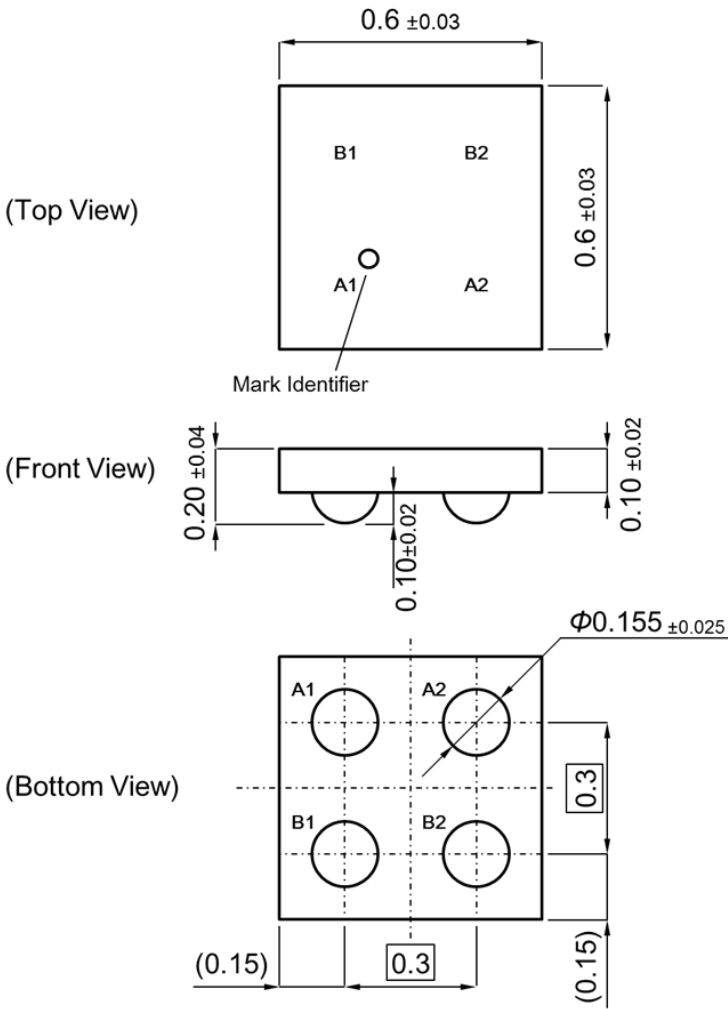


TECHNICAL DATA (Reference)



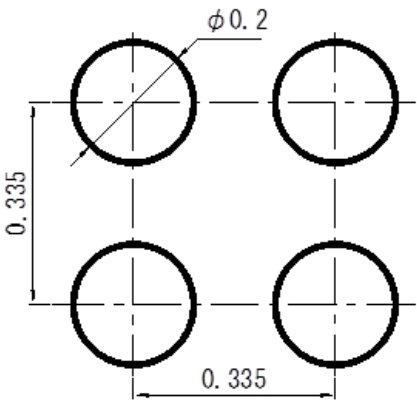
9. OUTLINE

Unit : mm



10. LAND PATTERN (Reference)

Unit : mm



11. REVISION HISTORY

Date	Revision	Description
2021.2.3	1.00	1. initially issued.

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